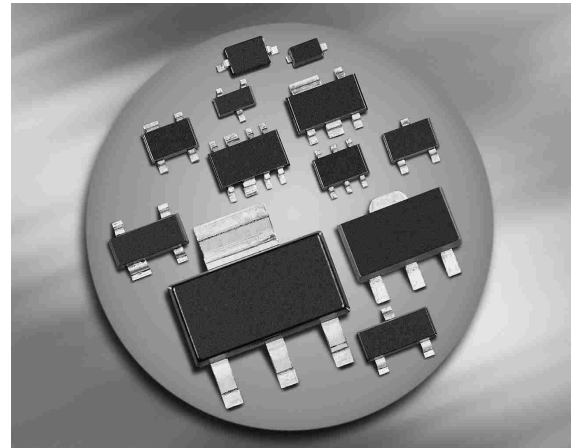
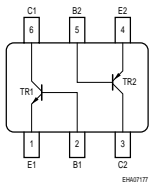


**NPN / PNP Silicon Switching Transistor Array**

- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN / PNP transistor in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101


**SMBT3904PN**  
**SMBT3904UPN**


Type	Marking	Pin Configuration						Package
		1=E	2=B	3=C	4=E	5=B	6=C	
SMBT3904PN	s3P	1=E	2=B	3=C	4=E	5=B	6=C	SOT363
SMBT3904UPN	s3P	1=E	2=B	3=C	4=E	5=B	6=C	SC74

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	40	V
Collector-base voltage	$V_{CBO}$	40	
Emitter-base voltage	$V_{EBO}$	6	
Collector current	$I_C$	200	mA
Total power dissipation- $T_S \leq 115\text{ °C}$ , SMBT3904PN $T_S \leq 105\text{ °C}$ , SMBT3904UPN	$P_{tot}$	250 330	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$		K/W
SMBT3904PN		≤ 140	
SMBT3904UPN		≤ 135	

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	40	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	40	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 30\text{ V}, I_E = 0$	$I_{CBO}$	-	-	50	nA
DC current gain <sup>2)</sup> $I_C = 100\text{ }\mu\text{A}, V_{CE} = 1\text{ V}$ $I_C = 1\text{ mA}, V_{CE} = 1\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 1\text{ V}$ $I_C = 50\text{ mA}, V_{CE} = 1\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1\text{ V}$	$h_{FE}$	40 70 100 60 30	- - - - -	- - 300 - -	-
Collector-emitter saturation voltage <sup>2)</sup> $I_C = 10\text{ mA}, I_B = 1\text{ mA}$ $I_C = 50\text{ mA}, I_B = 5\text{ mA}$	$V_{CEsat}$	- -	- -	0.25 0.4	V
Base emitter saturation voltage <sup>2)</sup> $I_C = 10\text{ mA}, I_B = 1\text{ mA}$ $I_C = 50\text{ mA}, I_B = 5\text{ mA}$	$V_{BEsat}$	0.65 -	- -	0.85 0.95	

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

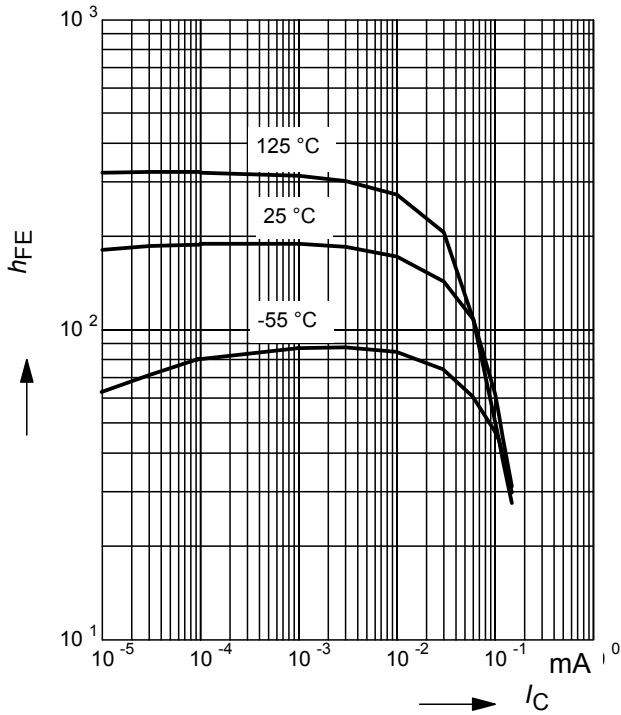
<sup>2)</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Transition frequency $I_C = 10\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 100\text{ MHz}$	$f_T$	250	-	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	-	3.5	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{eb}$	-	-	10	
Delay time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 1\text{ mA}$ , $V_{BE(off)} = 0.5\text{ V}$	$t_d$	-	-	35	ns
Rise time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = 1\text{ mA}$ , $V_{BE(off)} = 0.5\text{ V}$	$t_r$	-	-	35	
Storage time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = I_{B2} = 1\text{ mA}$	$t_{stg}$	-	-	225	
Fall time $V_{CC} = 3\text{ V}$ , $I_C = 10\text{ mA}$ , $I_{B1} = I_{B2} = 1\text{ mA}$	$t_f$	-	-	75	
Noise figure $I_C = 100\text{ }\mu\text{A}$ , $V_{CE} = 5\text{ V}$ , $f = 1\text{ kHz}$ , $\Delta f = 200\text{ Hz}$ , $R_S = 1\text{ k}\Omega$	$F$	-	-	5	dB

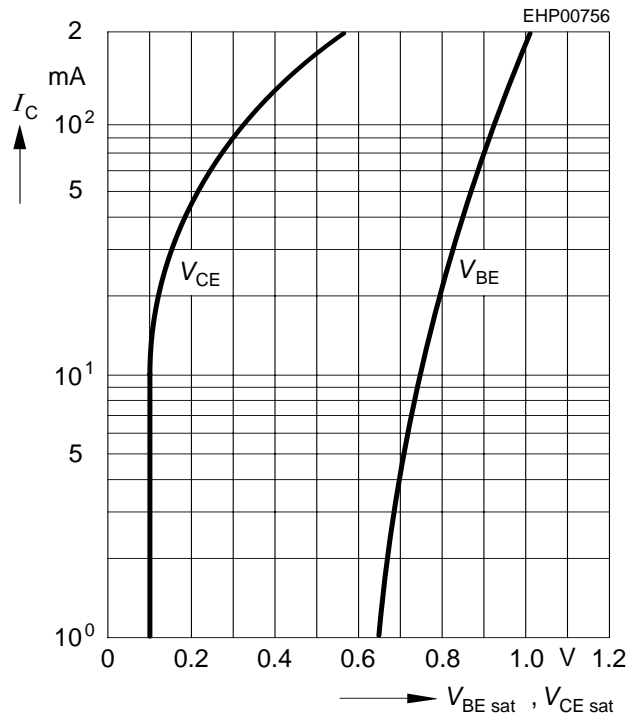
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 1\text{ V}$ , normalized



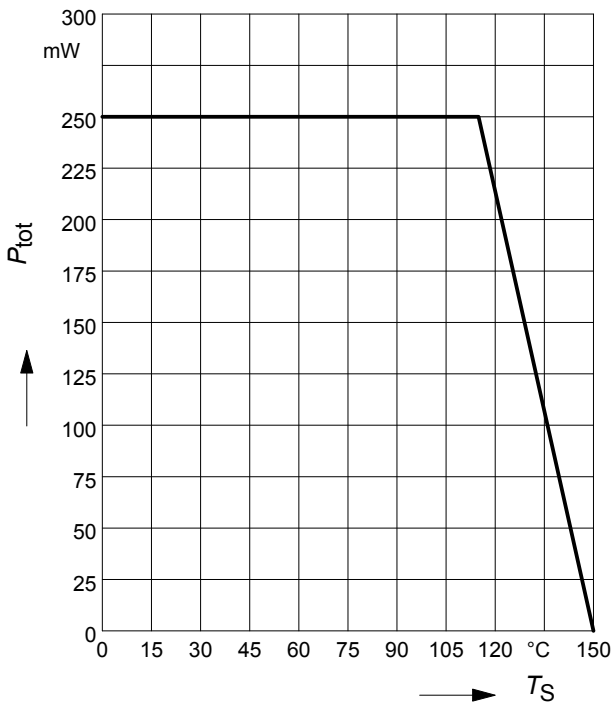
**Saturation voltage  $I_C = f(V_{BEsat}; V_{CEsat})$**

$h_{FE} = 10$



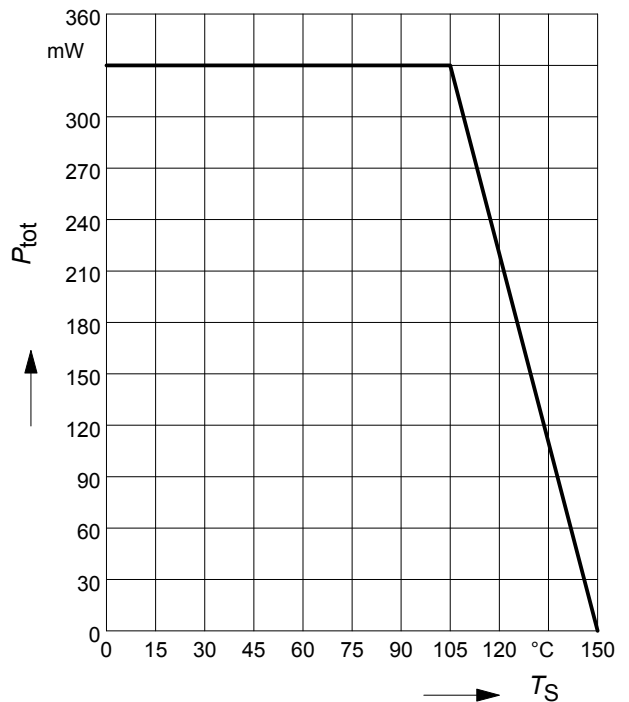
**Total power dissipation  $P_{tot} = f(T_S)$**

SMBT3904PN



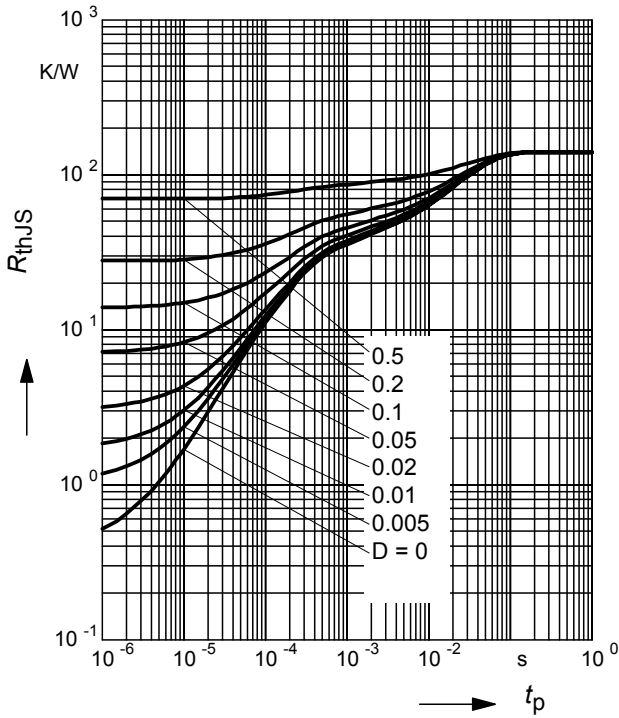
**Total power dissipation  $P_{tot} = f(T_S)$**

SMBT3904UPN



**Permissible Pulse Load  $R_{thJS} = f(t_p)$**

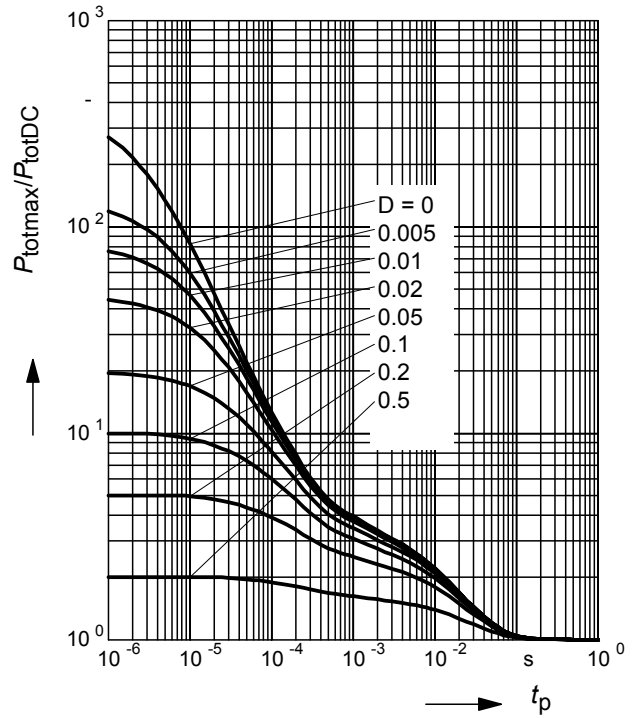
SMBT3904PN



**Permissible Pulse Load**

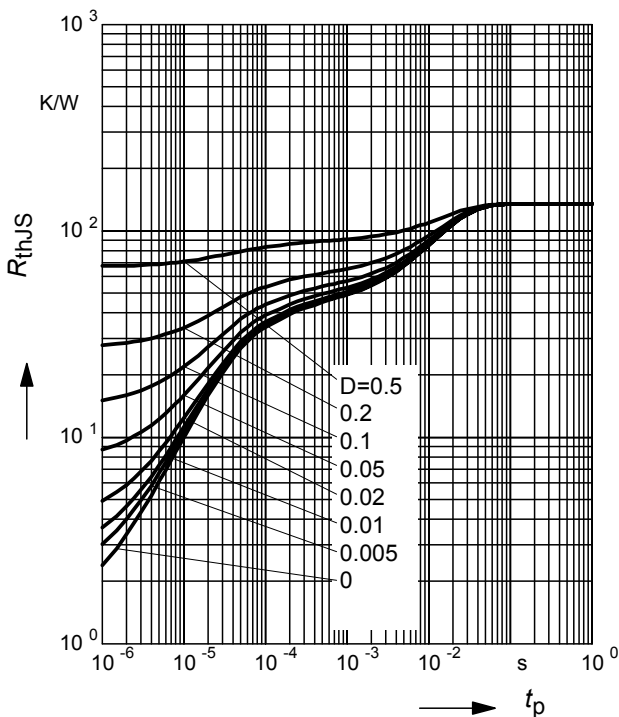
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3904PN



**Permissible Puls Load  $R_{thJS} = f(t_p)$**

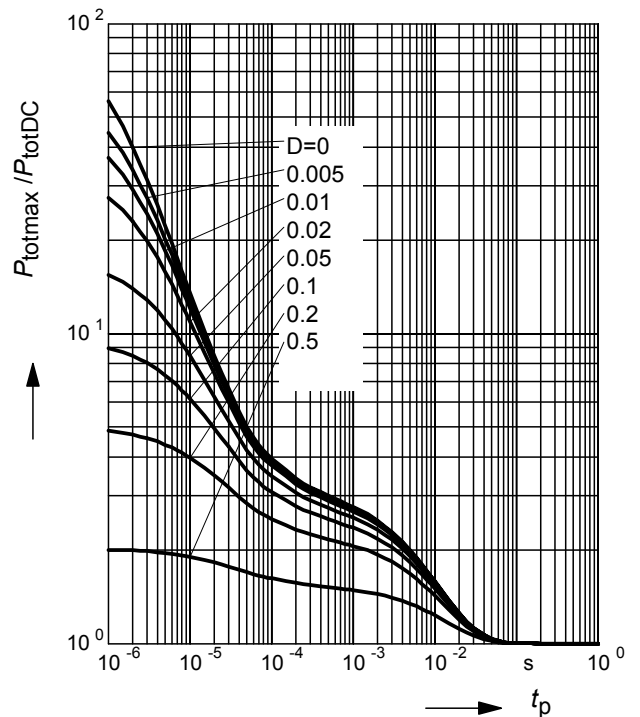
SMBT3904UPN



**Permissible Pulse Load**

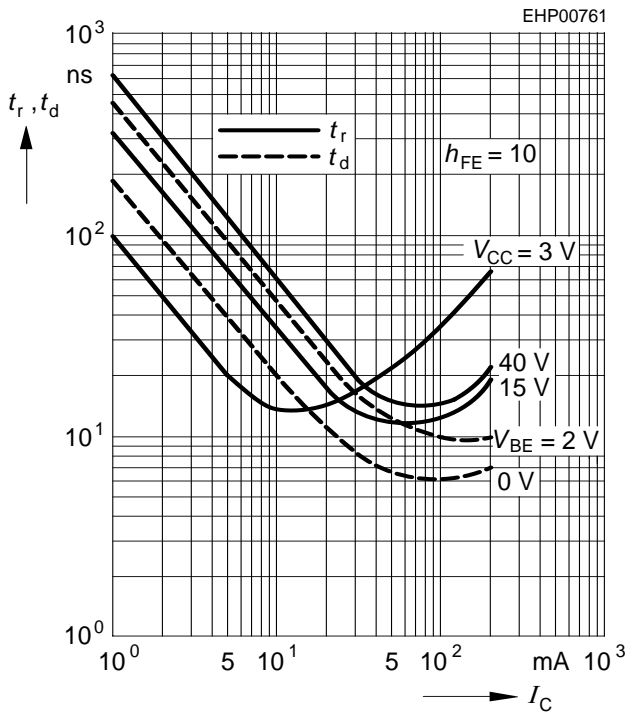
$P_{totmax}/P_{totDC} = f(t_p)$

SMBT3904UPN

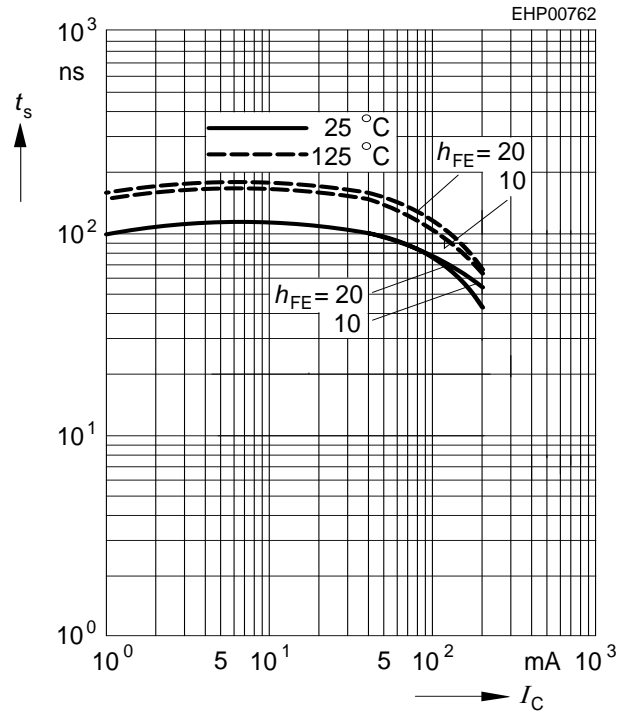


Delay time  $t_d = f(I_C)$

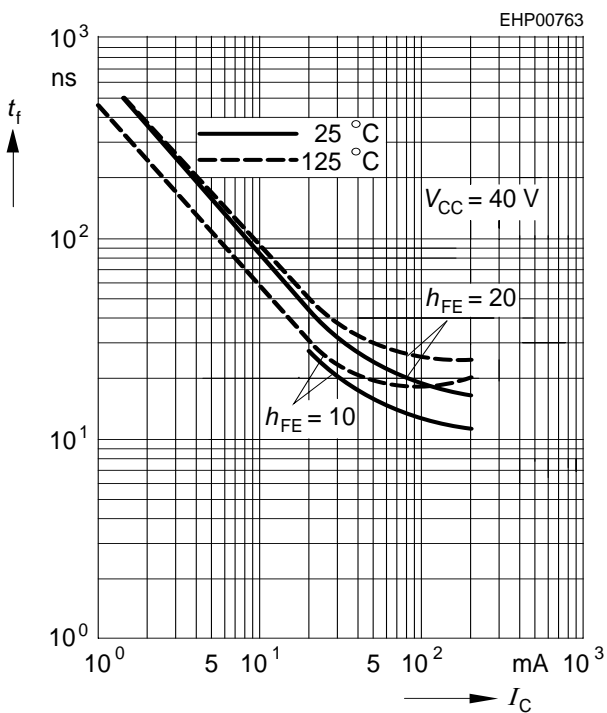
Rise time  $t_r = f(I_C)$



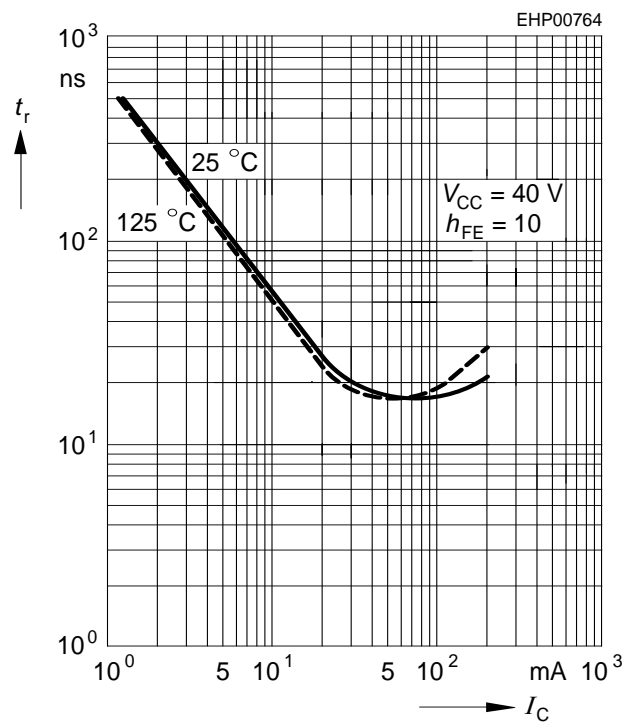
Storage time  $t_{stg} = f(I_C)$



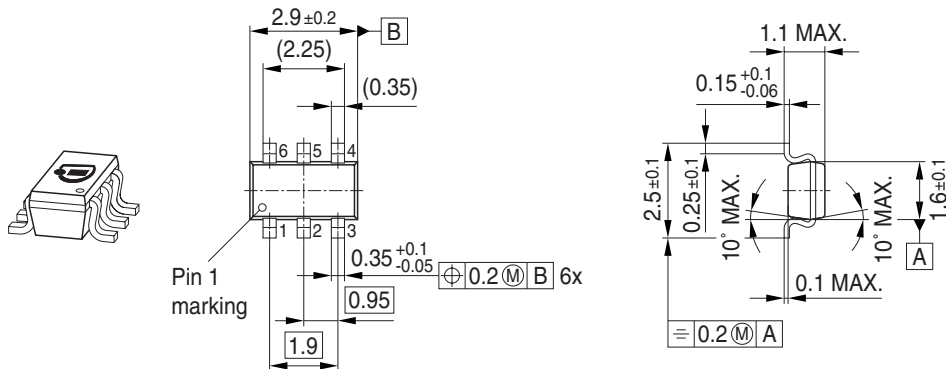
Fall time  $t_f = f(I_C)$



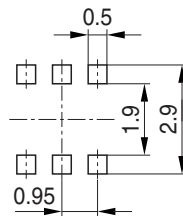
Rise time  $t_r = f(I_C)$



Package Outline

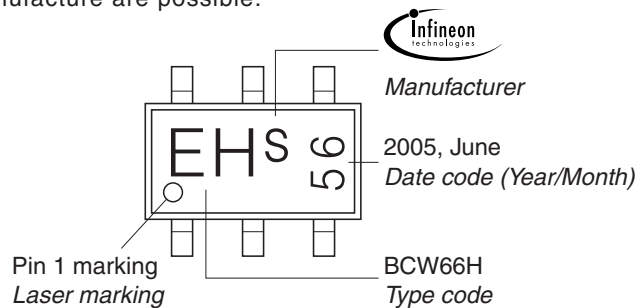


Foot Print



Marking Layout (Example)

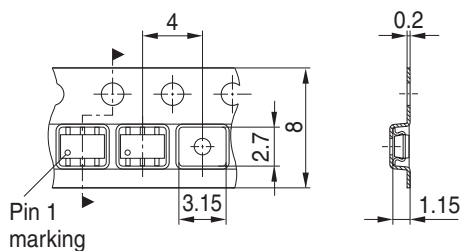
Small variations in positioning of Date code, Type code and Manufacture are possible.



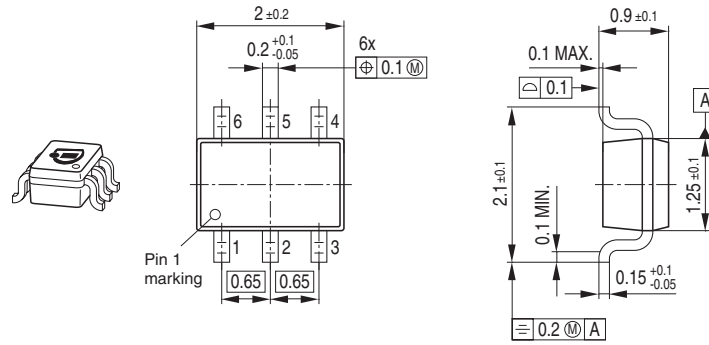
Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

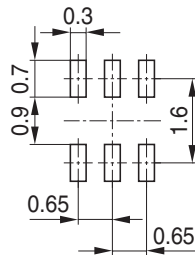
For symmetric types no defined Pin 1 orientation in reel.



Package Outline

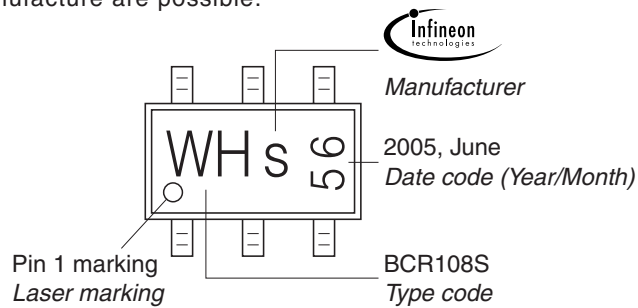


Foot Print



Marking Layout (Example)

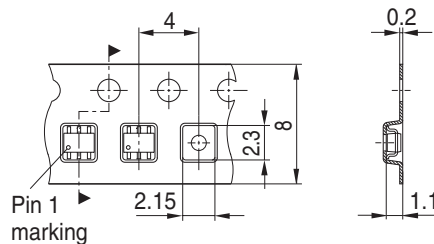
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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